

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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2SK3047

Silicon N-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed: EAS > 15 mJ
- \bullet Gate-source surrender voltage V_{GSS} : $\pm 30 \text{ V}$ guaranteed
- High-speed switching
- No secondary breakdown

■ Applications

- Non-contact relay
- · Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25$ °C

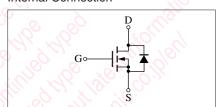
Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V _{DSS}	800	V	
Gate-source surrender voltage	V _{GSS}	±30	V	
Drain current	I_{D}	±2	A	
Peak drain current	I_{DP}	±4	A	
Avalanche energy capability *	EAS	15	mJ	
Power dissipation	P_{D}	30	W	
$T_a = 25^{\circ}C$		2		
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: L = 7.5 mH, $I_L = 2 \text{ A}$, 1 pulse

Unit: mm 4.6±0.2 2.9±0.2 0.5±0.15 1.4±0.2 1.6±0.2 1.6±0.1 0.55±0.15 1. Gate 2: Drain 3: Source TO-220D-A1 Package

Marking Symbol: K3047

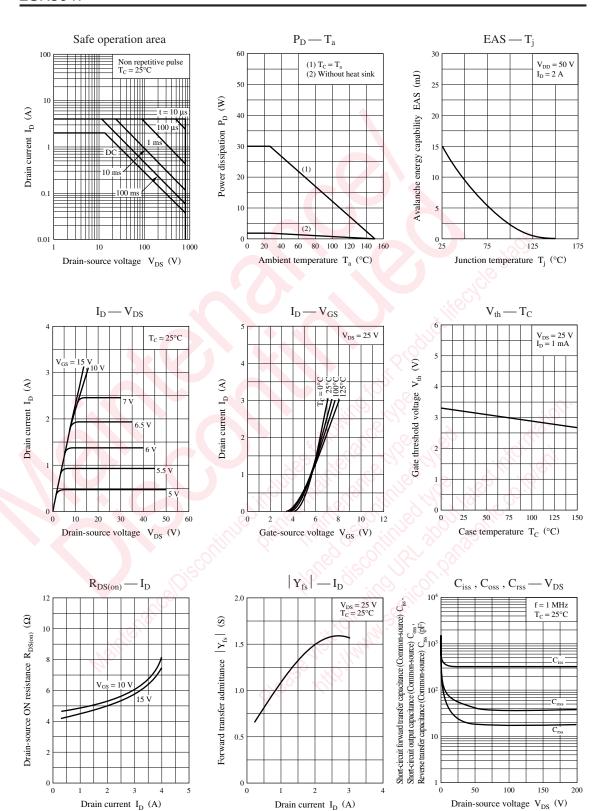
Internal Connection



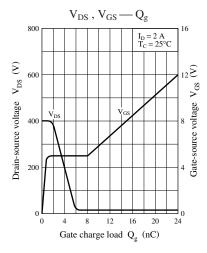
■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

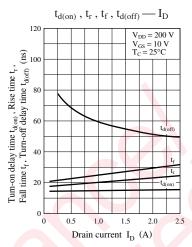
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	$V_{ m DSS}$	$I_D = 1 \text{ mA}, V_{GS} = 0$	800			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 640 \text{ V}, V_{GS} = 0$	1.7		100	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$			±1	μΑ
Gate threshold voltage	V _{th}	$V_{DS} = 25 \text{ V}, I_D = 1 \text{ mA}$	2.0		5.0	V
Forward transfer admittance	Yfs	$V_{DS} = 25 \text{ V}, I_D = 1 \text{ A}$	0.7	1.1		S
Drain-source ON resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$		4.8	7.0	Ω
Diode forward voltage	V _{DF}	$I_{DR} = 2 \text{ A}, V_{GS} = 0$			-1.3	V
Short-circuit forward transfer capacitance (Common source)	C _{iss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		350		pF
Short-circuit output capacitance (Common source)	C _{oss}	6/6, //		60		pF
Reverse transfer capacitance (Common source)	C _{rss}			25		pF
Turn-on delay time	t _{d(on)}	$V_{DD} = 200 \text{ V}, I_D = 1 \text{ A}, R_L = 200 \Omega$		15		ns
Rise time	t _r	$V_{GS} = 10 \text{ V}$		20		ns
Fall time	t _f			25		ns
Turn-off delay time	t _{d(off)}			60		ns
Thermal resistance (ch-c)	R _{th(ch-c)}				4.1	°C/W
Thermal resistance (ch-a)	R _{th(ch-a)}				62.5	°C/W

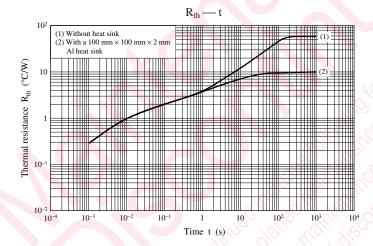
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



2 SJG00024BED







SJG00024BED 3

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